

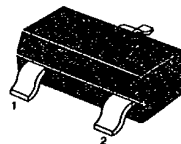
KSA1182**PNP EPITAXIAL SILICON TRANSISTOR****LOW FREQUENCY POWER AMPLIFIER**

• Complement to KSA2859

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-35	V
Collector-Emitter Voltage	V_{CE0}	-30	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-500	mA
Collector Dissipation	P_C	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ 150	$^\circ\text{C}$

SOT-23



1. Base 2. Emitter 3. Collector

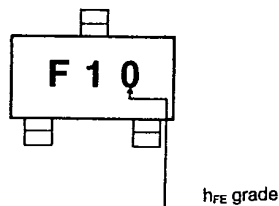
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -35\text{V}, I_E = 0$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC Current Gain	h_{FE1}	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	70		240	
	h_{FE2}	$V_{CE} = -6\text{V}, I_C = -400\text{mA}$	25			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$		-0.1	-0.25	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C = -100\text{mA}, V_{CE} = -1\text{V}$		-0.8	-1.0	V
Current Gain-Bandwidth Product	f_T	$I_C = -20\text{mA}, V_{CE} = -6\text{V}$		200		MHz
Output Capacitance	C_{ob}	$V_{CB} = -6\text{V}, I_E = 0$ $f = 1\text{MHz}$		13		pF

 h_{FE} CLASSIFICATION

Classification	O	Y
$h_{FE} (1)$	70-140	120-240

Marking

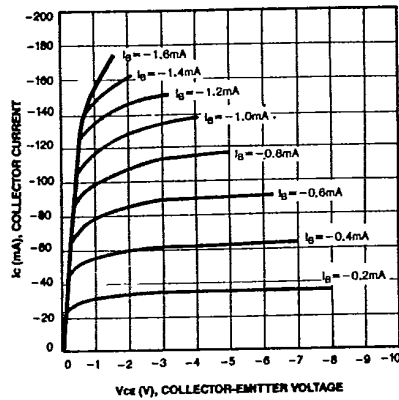
 h_{FE} grade

KSA1182

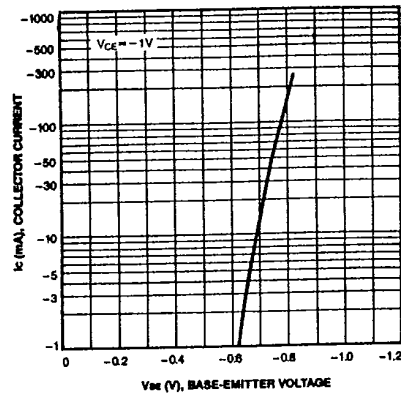
PNP EPITAXIAL SILICON TRANSISTOR

T-29-15

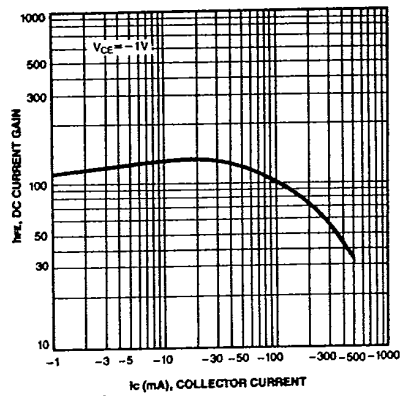
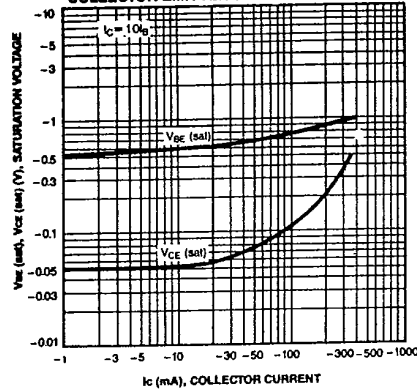
STATIC CHARACTERISTIC



BASE-EMITTER ON VOLTAGE



DC CURRENT GAIN

BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE

COLLECTOR OUTPUT CAPACITANCE

